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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tatsuya SHIMODA et al.

Application No.: 09/892,872

Filed: June 28, 2001



Group Art Unit: 2815

Examiner: B. Baumeister

Docket No.: 109975

For: FERROELECTRIC MEMORY AND METHOD OF MAKING THE SAME

AMENDMENT UNDER 37 C.F.R. §1.111

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed June 10, 2002, please amend the above-identified application as follows:

IN THE DRAWINGS:

Please amend Figures 24, 25 and 26A-26C as set forth in the attached Request for Approval of Drawing Corrections.

IN THE CLAIMS:

Please replace claims 1-3, 8-10, 12-14, 18 and 19 as follows:

- 31
1. (Twice Amended) A ferroelectric memory, comprising:
 - a microstructure;
 - a passive matrix array that includes memory cells formed of ferroelectric capacitors, the passive matrix array being formed on the microstructure;
 - a substrate, the microstructure being integrated on the substrate; and
 - a peripheral circuit for the passive matrix array, the peripheral circuit being separately formed on the substrate.